## **Supporting Information**

## Defect Engineering of Solution-Processed ZnO:Li Window Layer Towards High-Efficiency and Low-Cost Kesterite Photovoltaics

Qian Xiao<sup>a</sup>, Dongxing Kou<sup>a</sup>\*, Wenhui Zhou<sup>a</sup>, Zhengji Zhou<sup>a</sup>, Shengjie Yuan<sup>a</sup>, Yafang Qi<sup>a</sup>, Yuena Meng<sup>a</sup>, Litao Han<sup>a</sup>, Zhi Zheng<sup>b</sup>, and Sixin Wu<sup>a</sup>\*

<sup>a</sup> Key Lab for Special Functional Materials, Ministry of Education, National & Local Joint Engineering Research Center for High-Efficiency Display and Lighting Technology, School of Materials Science and Engineering, Collaborative Innovation Center of Nano Functional Materials and Applications, Henan University, Kaifeng 475004, China.

<sup>b</sup> Inst Surface Micro & Nano Mat, Coll Adv Mat & Energy, Key Lab Micronano Energy Storage & Convers Mat He, Xuchang University, Xuchang, Henan 461000, China.

E-mail: koudongxing@henu.edu.cn; wusixin@henu.edu.cn



Figure S1 Statistical box diagrams of J-V curves,  $J_{sc}$ ,  $V_{oc}$ , FF and PCE for CZTSSe solar cells with different ZnO NPs solution concentration.



Figure S2 Statistical box diagrams of  $J_{sc}$ ,  $V_{oc}$ , FF and PCE for CZTSSe solar cells at different ZnO NPs window layer annealing temperature.



**Figure S3.** The SEM top-view images of the (a) sputtered i-ZnO/CdS/CZTSSe stack and (d) ZnO NPs/CdS/CZTSSe stack. The surface EDS element mapping of (b) Zn and (c) O for i-ZnO and (e) Zn and (f) O for ZnO NPs.



Figure S4 The resistivity  $\rho$  of sputtered i-ZnO and ZnO:Li NPs films with different Li content on soda-lime glass.



**Figure S5** (a)-(b) are the shunt resistance and (c)-(d) are the series resistance of CZTSSe solar cells using ZnO NPs and ZnO:Li NPs window layer, respectively.



**Figure S6.** (a) EQE curves of CZTSSe solar cells using ZnO NPs and ZnO:Li NPs window layer. (b) The EQE difference ( $\Delta$ EQE) of the CZTSSe solar cells before and after 2% Li doping.



**Figure S7** (a) The *J-V* curves of CZTSSe solar cells with 2% Li doping ZnO layer before and after 60 days storage. (b) The efficiency stability within 60 days for the champion CZTSSe device with 2% Li doping ZnO layer.



Figure S8 XRD of the pristine ZnO NPs and 2% ZnO:Li NPs films deposited on ITO glass.

$$q = \frac{2\pi}{d} = \frac{4\pi \sin\theta}{\lambda}$$
$$\frac{1}{d_{hkl}^2} = \frac{4}{3} \left( \frac{h^2 + hk + k^2}{a^2} \right) + \frac{l^2}{c^2}$$

 $\lambda$ =1.5406 nm, a, b and c are cell parameters, (hkl) is the crystal face index, *d* is the interplanar spacing and  $2\theta$  is the diffraction angle. The unit cell parameters of ZnO wurtzite follow the principle that a=b $\neq$ c,  $\alpha$ = $\beta$ =90°,  $\gamma$ =120°. For the main peak (002) plane, the lattice parameters of pristine ZnO and ZnO:Li NPs are evaluated to be a=b=3.4216, c=5.4547 and a=b=3.4340, c=5.4830, respectively.



Figure S9  $Li_{1s}$  of XPS for the pristine ZnO NPs and 2% ZnO:Li NPs films deposited on glass.



Figure S10. EPR of sputtered i-ZnO and solution-processed ZnO NPs films.



**Figure S11** SEM cross-section morphologies of the (a) i-ZnO, (b) one layer of ZnO NPs films, (c) two layers of ZnO NPs films and (d) three layers of ZnO NPs films deposited on soda-lime glass.



**Figure S12** Transmittance spectrum of the sputtered ZnO, pristine ZnO NPs (1, 2, 3 layers) and ZnO:Li NPs (2 layers) films deposited on soda-lime glass.



**Figure S13** EIS Nyquist diagrams for the CZTSSe solar cells with i-ZnO and ZnO NPs window layers measured under -0.45 V.



Figure S14 PL of pristine ZnO NPs and 2% ZnO:Li NPs films.



Figure S15 Two dimensional atomic force microscopy images of ZnO NPs/CdS /CZTSSe stack and ZnO:Li NPs/CdS/CZTSSe stack.



Figure S16 Cross-section scanning morphology of EBIC for the CZTSSe solar cells using ZnO NPs and ZnO:Li NPs window layer.



Figure S17 (a) The temperature-dependent ideal factor A of CZTSSe solar cells with ZnO NPs and 2% Li doping ZnO layers with the range of 350-100 K under dark condition.